

1/5

100

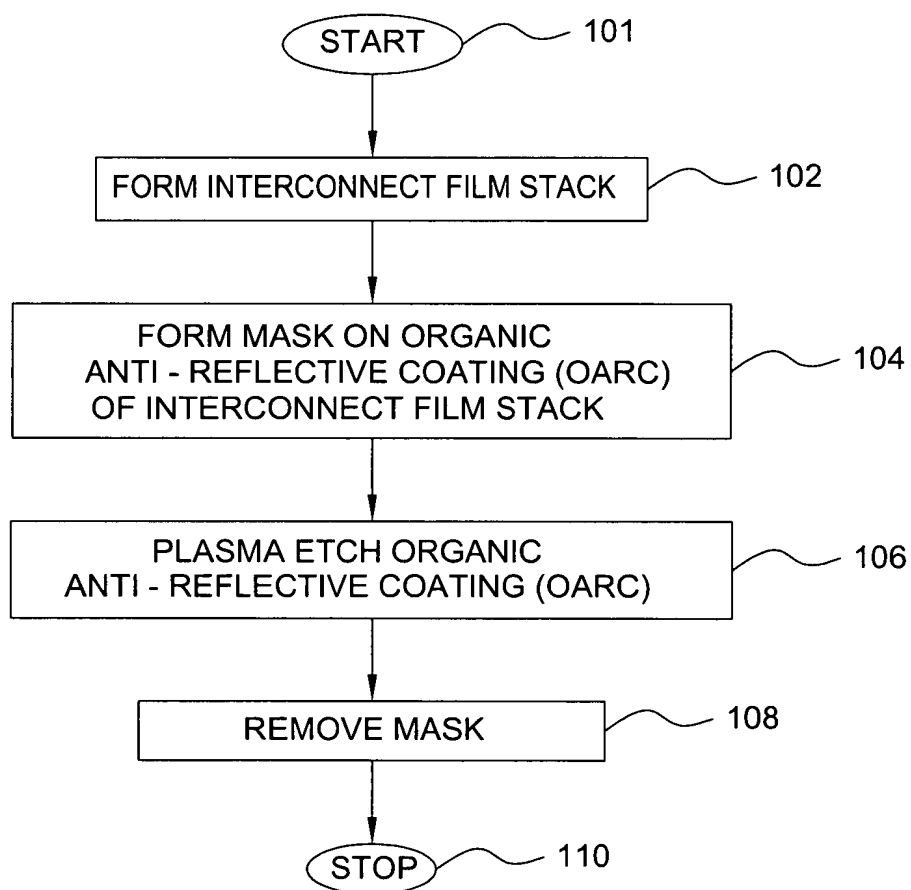


FIG. 1

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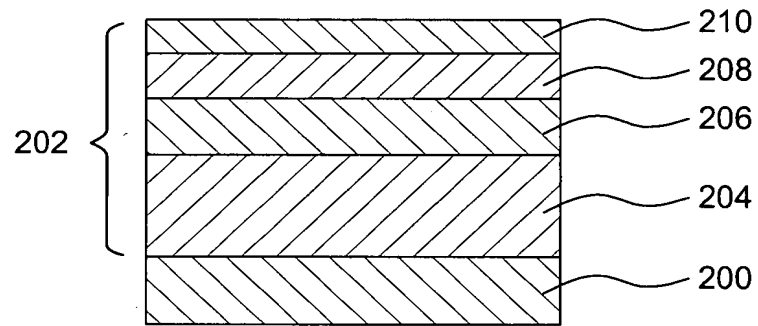


FIG. 2A

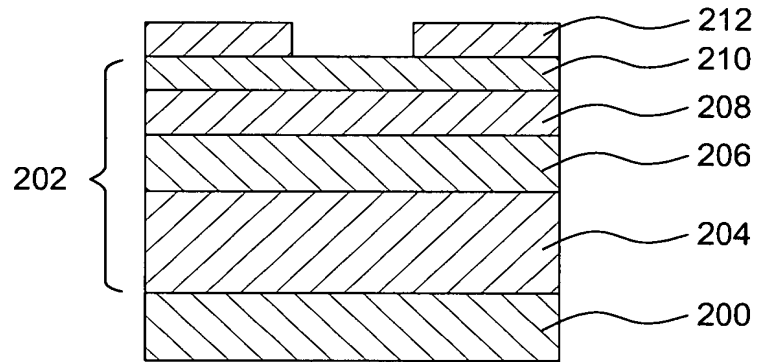


FIG. 2B

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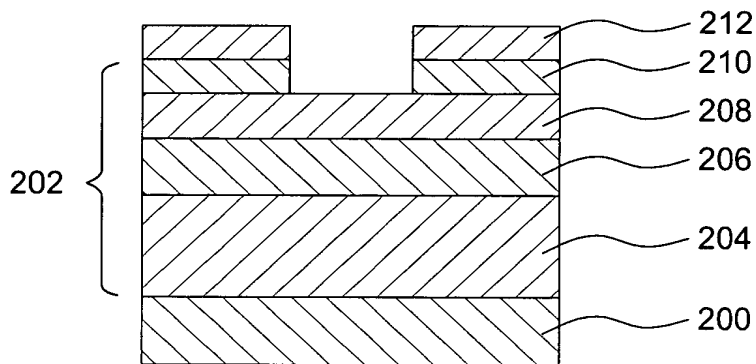


FIG. 2C

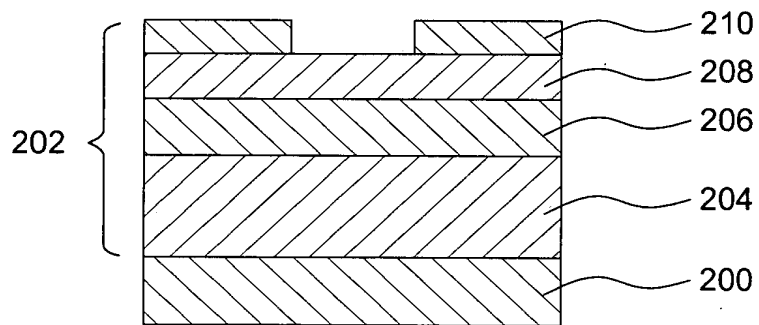


FIG. 2D



PLASMA ETCH PROCESS OF THE PRESENT INVENTION				
PARAMETER	PROCESS RANGES			EXAMPLE
	UNITS	MIN	MAX	
HYDROCARBON GAS (2.7% C ₂ H ₄ IN HELIUM)	SCCM	30	200	50
INERT GAS (N ₂)	SCCM	10	600	5
CHAMBER PRESSURE	mTorr	1	30	2
SUBSTRATE TEMPERATURE	DEGREES CELSIUS	10	60	40
SUBSTRATE BIAS POWER	W	50	200	100
PLASMA POWER	W	500	1200	600

FIG. 4